

## N-Channel 1.2 V (G-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
8	0.031 at V <sub>GS</sub> = 4.5 V	12.2	20 nC
	0.033 at V <sub>GS</sub> = 2.5 V	11.6	
	0.035 at V <sub>GS</sub> = 1.8 V	11.2	
	0.043 at V <sub>GS</sub> = 1.5 V	10.2	
	0.077 at V <sub>GS</sub> = 1.2 V	1.3	

### FEATURES

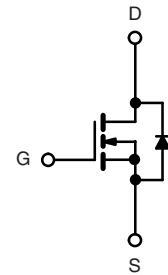
- TrenchFET<sup>®</sup> Power MOSFET
- Industry First 1.2 V Rated MOSFET
- Ultra Small MICRO FOOT<sup>®</sup> Chipscale Packaging Reduces Footprint Area, Profile (0.62 mm) and On-Resistance Per Footprint Area
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



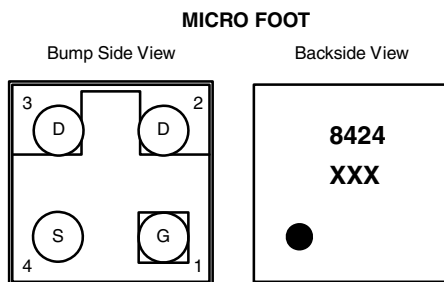
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Low Threshold Load Switch for Portable Devices
  - Low Power Consumption
  - Increased Battery Life
- Ultra Low Voltage Load Switch



N-Channel MOSFET



**Device Marking:** 8424  
xxx = Date/Lot Traceability Code

**Ordering Information:** Si8424DB-T1-E1 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	8	V
Gate-Source Voltage	V <sub>GS</sub>	± 5	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	12.2
		T <sub>C</sub> = 70 °C	9.8
		T <sub>A</sub> = 25 °C	8.1 <sup>b,c</sup>
		T <sub>A</sub> = 70 °C	6.5 <sup>b,c</sup>
Pulsed Drain Current	I <sub>DM</sub>	20	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	2.3 <sup>b,c</sup>
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	6.25
		T <sub>C</sub> = 70 °C	4
		T <sub>A</sub> = 25 °C	2.78 <sup>b,c</sup>
		T <sub>A</sub> = 70 °C	1.78 <sup>b,c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C
Package Reflow Conditions <sup>d</sup>	IR/Convection	260	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Refer to IPC/JEDEC (J-STD-020), no manual or hand soldering.
- In this document, any reference to the Case represents the body of the MICRO FOOT device and Foot is the bump.

**THERMAL RESISTANCE RATINGS**

Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>a,b</sup>	$R_{thJA}$	35	45	°C/W
Maximum Junction-to-Foot (Drain)	Steady State $R_{thJF}$	16	20	

## Notes

a. Surface mounted on 1" x 1" FR4 board.

b. Maximum under steady state conditions is 72 °C/W.

**SPECIFICATIONS** ( $T_J = 25\text{ °C}$ , unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	8			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		8.9		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		- 2.5			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.35		1	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = 5\text{ V}$			100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 8\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 8\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ °C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = 4.5\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 1\text{ A}$		0.025	0.031	$\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 1\text{ A}$		0.027	0.033	
		$V_{GS} = 1.8\text{ V}, I_D = 1\text{ A}$		0.029	0.035	
		$V_{GS} = 1.5\text{ V}, I_D = 1\text{ A}$		0.032	0.043	
		$V_{GS} = 1.2\text{ V}, I_D = 1\text{ A}$		0.049	0.077	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 4\text{ V}, I_D = 1\text{ A}$		8.3	13	S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 4\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1950		pF
Output Capacitance	$C_{oss}$		610			
Reverse Transfer Capacitance	$C_{rss}$		350			
Total Gate Charge	$Q_g$	$V_{DS} = 4\text{ V}, V_{GS} = 5\text{ V}, I_D = 1\text{ A}$		22	33	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 4\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 1\text{ A}$		20	30	
Gate-Drain Charge	$Q_{gd}$		3.5			
Gate Resistance	$R_g$		1.8			
Gate Resistance	$R_g$	$V_{GS} = 0.1\text{ V}, f = 1\text{ MHz}$		13		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 4\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		8	12	ns
Rise Time	$t_r$		12	18		
Turn-Off Delay Time	$t_{d(off)}$		110	165		
Fall Time	$t_f$		40	60		

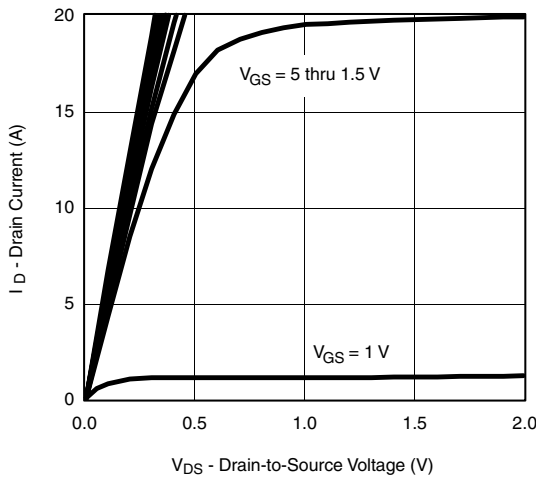
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			6.25	A
Pulse Diode Forward Current	$I_{SM}$				20	
Body Diode Voltage	$V_{SD}$	$I_S = 1\text{ A}, V_{GS} = 0\text{ V}$		0.6	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -1\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		104	156	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			88	132	nC
Reverse Recovery Fall Time	$t_a$			26		ns
Reverse Recovery Rise Time	$t_b$			78		

Notes:

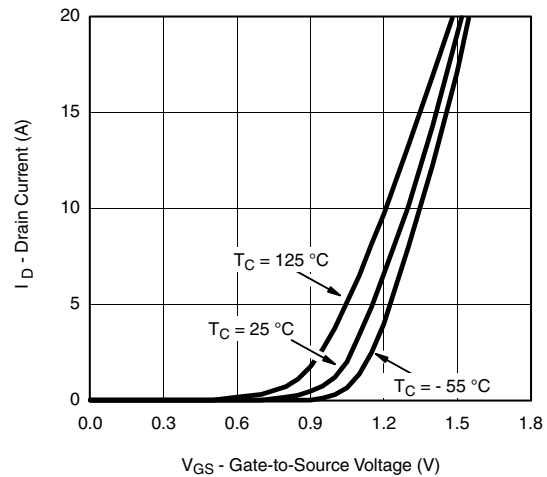
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### TYPICAL CHARACTERISTICS ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

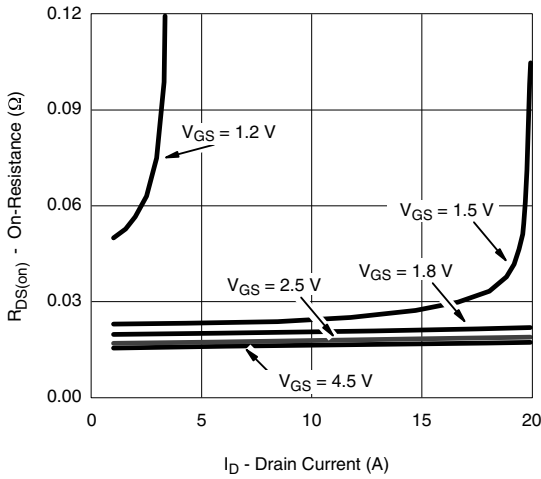


**Output Characteristics**

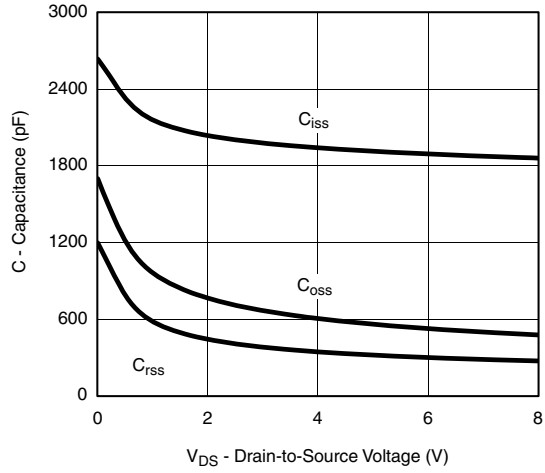


**Transfer Characteristics**

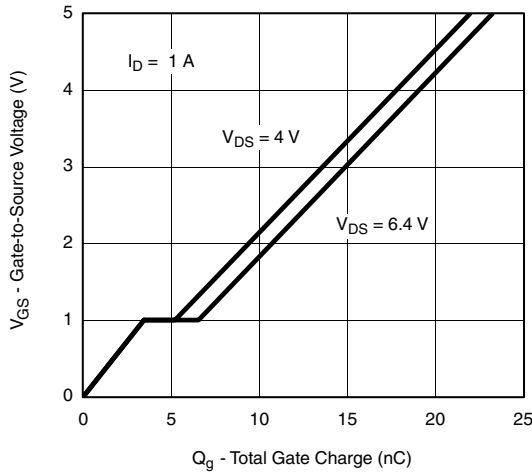
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



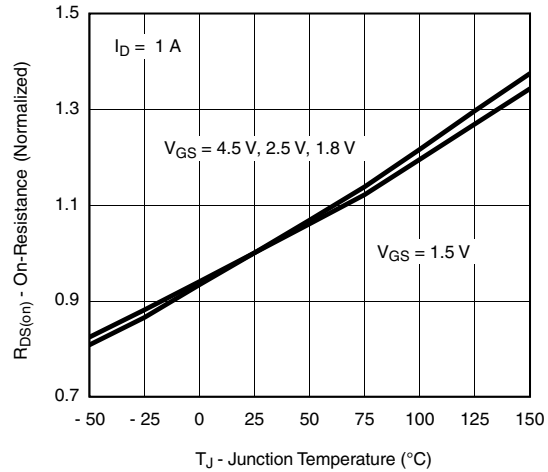
**$R_{DS(on)}$  vs. Drain Current**



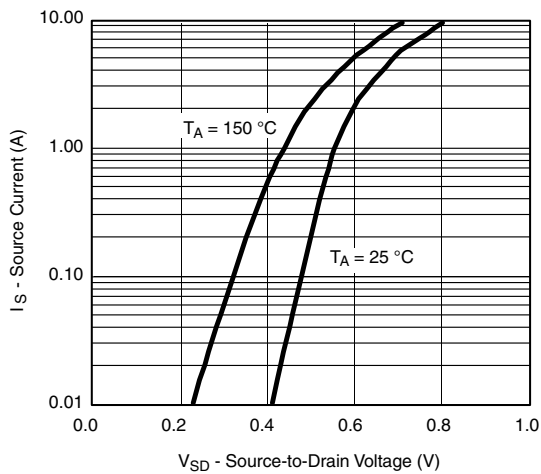
**Capacitance**



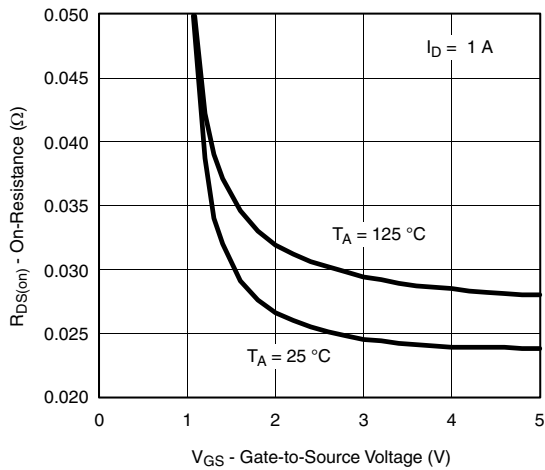
**Gate Charge**



**On-Resistance vs. Junction Temperature**

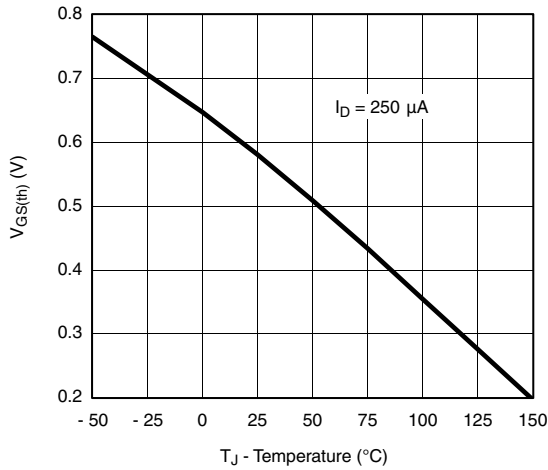


**Forward Diode Voltage vs Temp**

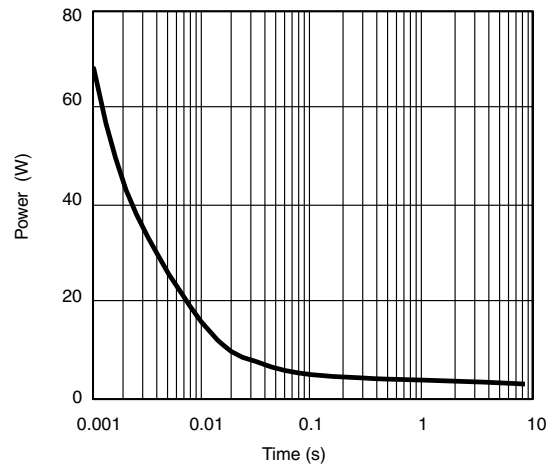


**$R_{DS(on)}$  vs  $V_{GS}$  vs Temperature**

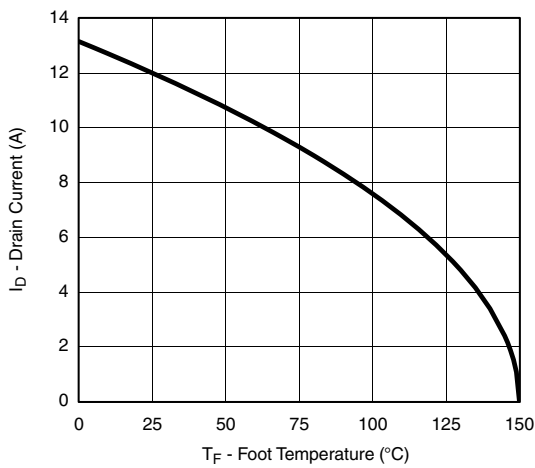
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



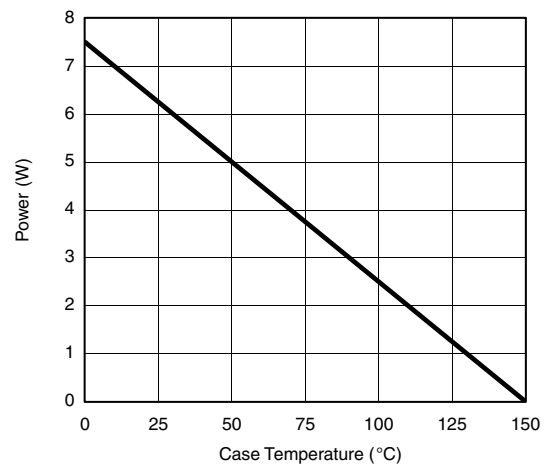
**Threshold Voltage**



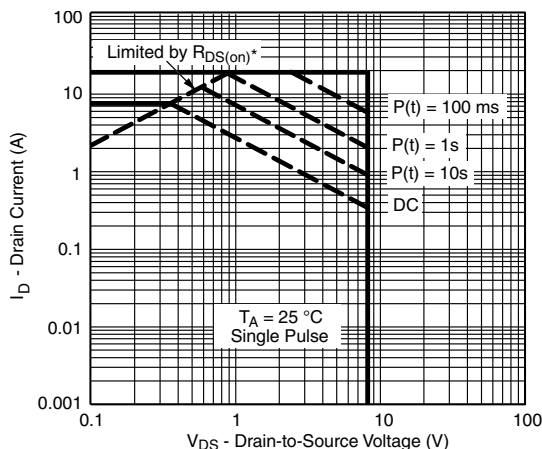
**Single Pulse Power, Junction-to-Ambient**



**Current Derating\*\***



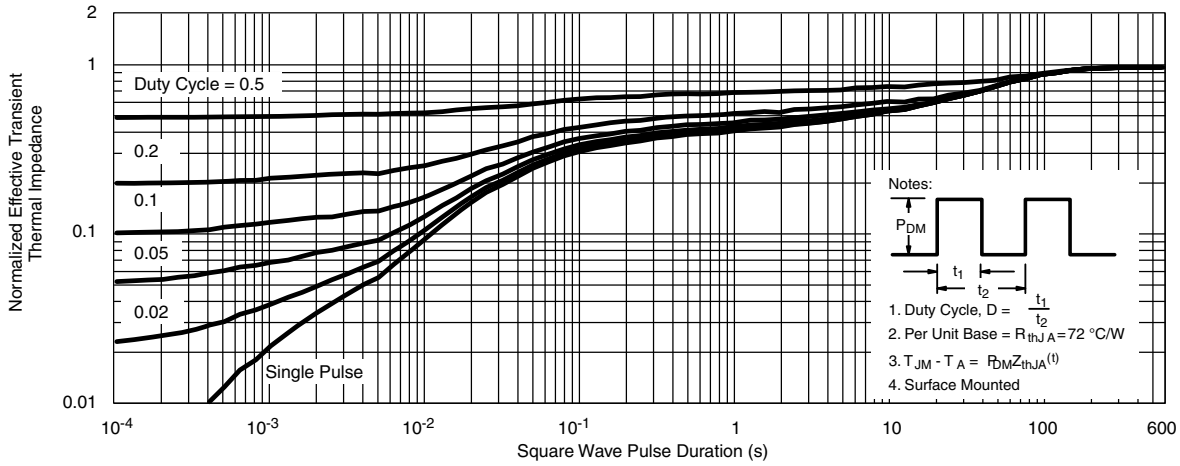
**Power Derating**



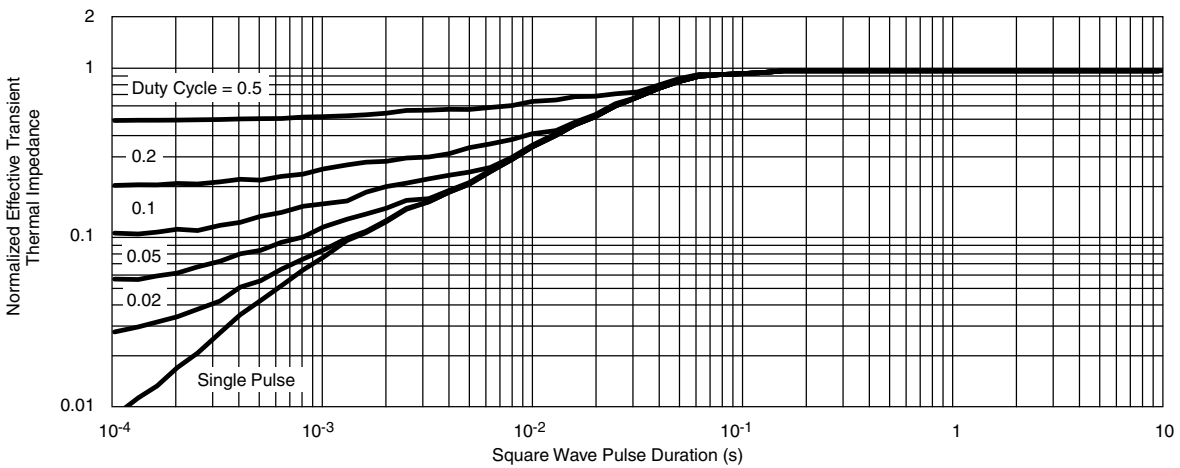
**Safe Operating Area, Junction-to-Ambient**

\*\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150\text{ }^\circ\text{C}$ , using junction-to-foot thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



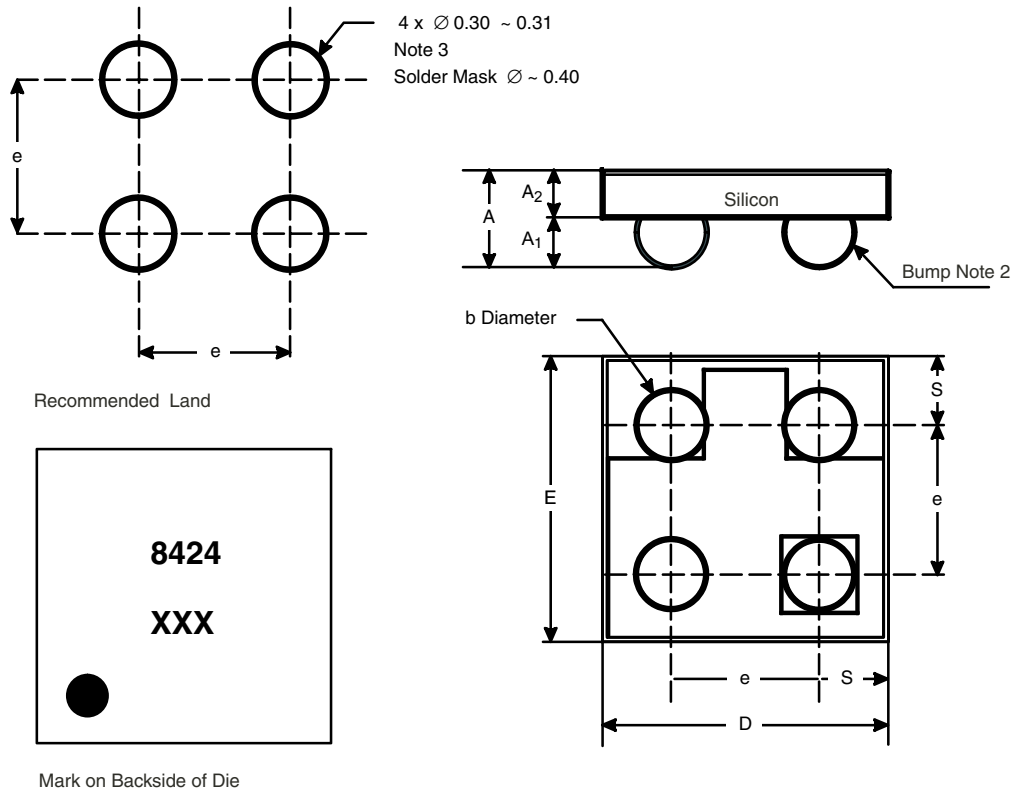
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

**PACKAGE OUTLINE**

**MICRO FOOT: 4-BUMP (0.8-mm PITCH)**



- Notes (unless otherwise specified):
1. Laser mark on the silicon die back, coated with a thin metal.
  2. Bumps are Sn/Ag/Cu.
  3. Non-solder mask defined copper landing pad.
  4. The flat side of wafers is oriented at the bottom.

Dim.	Millimeters <sup>a</sup>		Inches	
	Min.	Max.	Min.	Max.
A	0.600	0.650	0.0236	0.0256
A <sub>1</sub>	0.260	0.290	0.0102	0.0114
A <sub>2</sub>	0.340	0.360	0.0134	0.0142
b	0.370	0.410	0.0146	0.0161
D	1.520	1.600	0.0598	0.0630
E	1.520	1.600	0.0598	0.0630
e	0.800		0.0315	
S	0.360	0.400	0.0142	0.0157

Note:  
a. Use millimeters as the primary measurement.

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